

“HALF-BRIDGE” IGBT

Feature

- IGBT New Technology
- Low $V_{CE(sat)}$
- Low Turn-off losses
- Short tail current
- Positive temperature coefficient

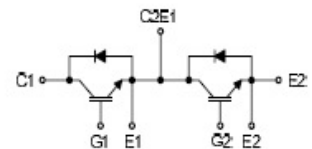
Application

- AC & DC Motor controls
- General purpose inverters
- Optimized for high current inverter
(AC TIG welding machines)
- Servo controls
- UPS, Robotics



Package : V1

$V_{CES} = 1200V$
 $I_c = 100A$
 $V_{CE(sat)} \text{ typ.} = 1.8V$



Absolute Maximum Ratings @ $T_j = 25^\circ C$ (Per Leg)

Symbol	Parameter	Condition	Ratings	Unit
V_{CES}	Collector to emitter voltage	$V_{GS} = 0V, I_c = 4mA$	1200	V
V_{GE}	Gate emitter voltage		± 20	V
I_c	Continuous collector current	$T_c = 75^\circ C (25^\circ C)$	100 (140)	A
I_{cP}	Pulsed collector current	$T_c = 25^\circ C$	200	A
I_F	Diode continuous forward current	$T_c = 75^\circ C (25^\circ C)$	100 (140)	A
I_{FM}	Diode maximum forward current	$T_c = 25^\circ C$	200	A
V_{iso}	Isolation voltage test	AC @ 1 minute	2500	V
T_j	Junction temperature		$-40 \sim 150$	$^\circ C$
T_{stg}	Storage temperature		$-40 \sim 125$	$^\circ C$
Weight	Weight of module		190	g
Md	Mounting torque with screw : M5		2.0	N.m
	Terminal connection torque : M5		2.0	N.m

Static Characteristics @ $T_j = 25^\circ C$ (unless otherwise specified)

Parameters		Min	Typ	Max	Unit	Test conditions
$V_{CE(sat)}$	Collector to emitter saturation voltage	1.3	1.8	2.3	V	$I_c = 100A, V_{GE} = 15V$
$V_{GE(th)}$	Gate threshold voltage	5.0	5.8	6.5		$V_{CE} = V_{GE}, I_c = 2mA$
I_{CES}	Zero gate voltage collector current	—	—	1.0	mA	$V_{GE} = 0V, V_{CE} = 1200V$
I_{GES}	Gate to emitter leakage current	—	—	600	nA	$V_{CE} = 0V, V_{GE} = 20V$
V_F	Diode forward voltage drop	1.3	1.7	2.1	V	$I_F = 100A$

Electrical Characteristics (IGBT / DIODE) @ $T_j = 25^\circ\text{C}$ (unless otherwise specified)

Parameters		Min	Typ	Max	Unit	Test conditions
C_{iss}	Input capacitance	—	7200	—	pF	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$ $f = 1\text{ MHz}$
C_{oss}	Output capacitance	—	400	—		
C_{rss}	Reverse transfer capacitance	—	300	—		
$t_{d(on)}$	Turn-on delay time	—	290	—	ns	$T_j = 125^\circ\text{C}$, $V_{CC} = 600\text{V}$ $I_C = 100\text{A}$, $V_{GE} = \pm 15\text{V}$ $R_G = 3.9\Omega$
t_r	Rise time	—	50	—		
$t_{d(off)}$	Turn-off delay time	—	590	—		
t_f	Fall time	—	90	—		
V_{BR}	Maximum peak repetitive reverse voltage	1200	—	—	V	$I_R = 4\text{mA}$
I_{RM}	Maximum reverse leakage current	—	—	250	μA	$V_R = 1200\text{V}$
t_{rr}	Reverse recovery time	—	170	—	ns	$I_F = 100\text{A}$, $V_R = 600\text{V}$ $di/dt = 2000\text{A}/\mu\text{s}$
Q_{rr}	Reverse recovery charge	—	9	—	μC	

Thermal Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-Case (IGBT Part, Per 1/2 Module)	-	-	0.26	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction-to-Case (Diode Part, Per 1/2 Module)	-	-	0.48	
$R_{\theta CS}$	Case-to-Heat Sink (Conductive grease applied)	-	0.05	-	

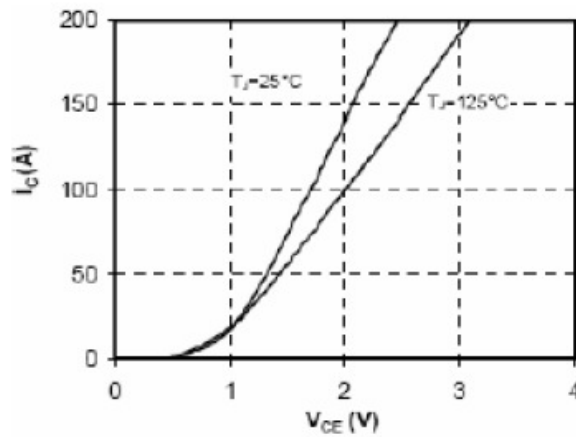


Fig 1. Typ. IGBT Output Characteristics

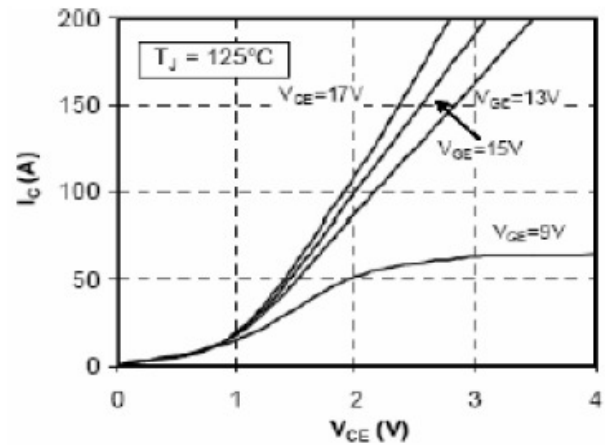


Fig 2. Typ. IGBT Output Characteristics

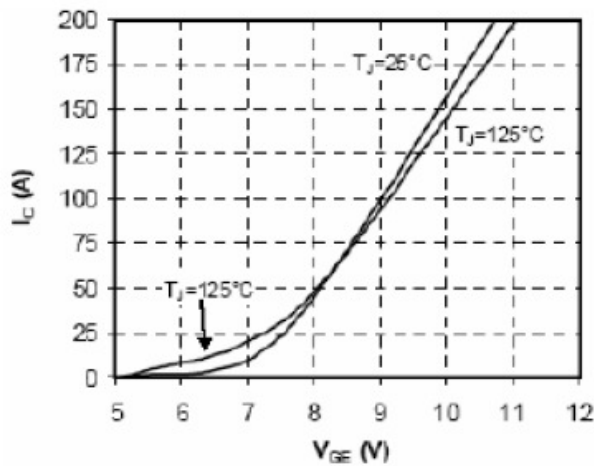


Fig 3. Typ. Transfer Characteristics

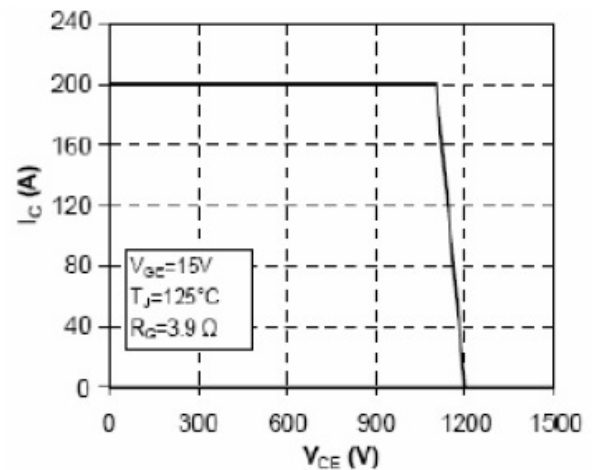


Fig 4. Reverse Bias Safe Operation Area

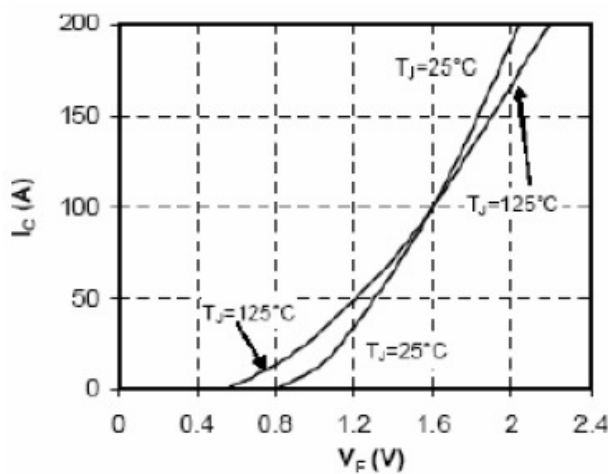


Fig 5. Forward Characteristics of Diode

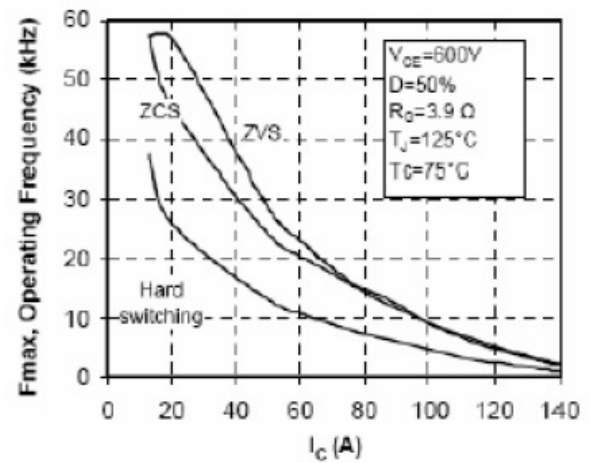
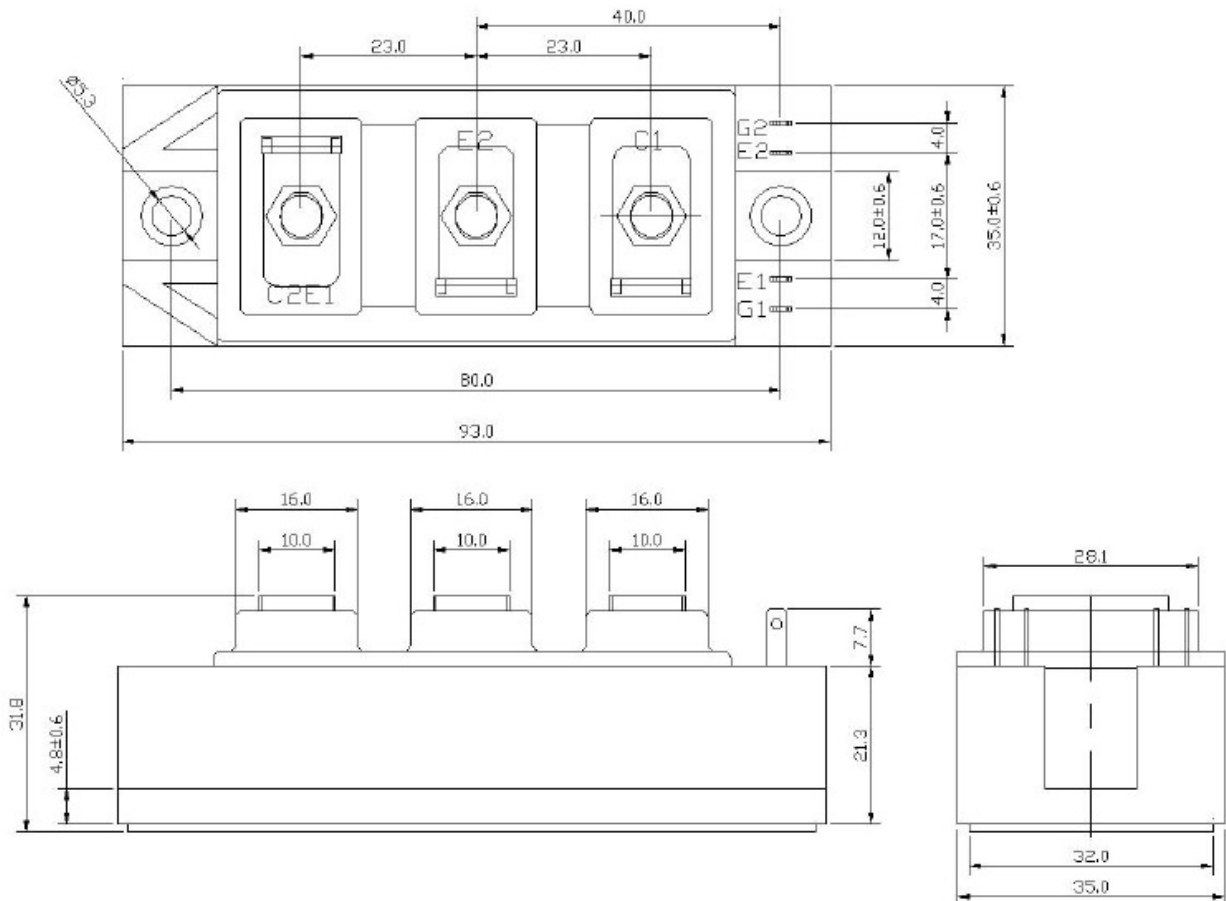


Fig 6. Operating Frequency vs. Collector Current

Package Outline (dimensions in mm)



* Data and specifications subject to change without notice.